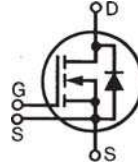


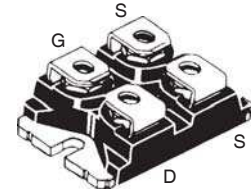
**Polar3™ HiPerFET™  
Power MOSFET**
**IXFN210N30P3**

$$\begin{aligned}
 V_{DSS} &= 300V \\
 I_{D25} &= 192A \\
 R_{DS(on)} &\leq 14.5m\Omega \\
 t_{rr} &\leq 250ns
 \end{aligned}$$

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier



miniBLOC  
E153432



G = Gate      D = Drain  
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

| Symbol        | Test Conditions  | Maximum Ratings |                  |
|---------------|--|-----------------|------------------|
| $V_{DSS}$     | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                          | 300             | V                |
| $V_{DGR}$     | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 300             | V                |
| $V_{GSS}$     | Continuous   | $\pm 20$        | V                |
| $V_{GSM}$     | Transient  | $\pm 30$        | V                |
| $I_{D25}$     | $T_C = 25^\circ\text{C}$   | 192             | A                |
| $I_{DM}$      | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 550             | A                |
| $I_A$         | $T_C = 25^\circ\text{C}$   | 105             | A                |
| $E_{AS}$      | $T_C = 25^\circ\text{C}$   | 4               | J                |
| $dv/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 35              | V/ns             |
| $P_D$         | $T_C = 25^\circ\text{C}$   | 1500            | W                |
| $T_J$         |  | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$      |  | 150             | $^\circ\text{C}$ |
| $T_{stg}$     |  | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$         | 1.6mm (0.062 in.) from Case for 10s                                      | 300             | $^\circ\text{C}$ |
| $T_{SOLD}$    | Plastic Body for 10s   | 260             | $^\circ\text{C}$ |
| $V_{ISOL}$    | 50/60 Hz, RMS, $t = 1$ minute  | 2500            | V~               |
|               | $I_{ISOL} \leq 1\text{mA}$ , $t = 1\text{s}$                             | 3000            | V~               |
| $M_d$         | Mounting Torque for Base Plate   | 1.5/13          | Nm/lb.in.        |
|               | Terminal Connection Torque   | 1.3/11.5        | Nm/lb.in.        |
| <b>Weight</b> |  | 30              | g                |

**Features**

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Dynamic  $dv/dt$  Rating
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$
- Low Drain-to-Tab Capacitance
- Low Package Inductance

**Advantages**

- Easy to Mount
- Space Savings

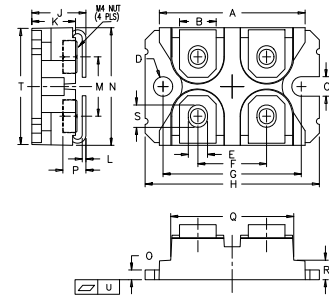
**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values |      |                            |
|--------------|---|-----------------------|------|----------------------------|
|              |   | Min.                  | Typ. | Max.                       |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 3\text{mA}$  | 300                   |      | V                          |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8\text{mA}$                                    | 2.5                   |      | 5.0 V                      |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$  |                       |      | $\pm 200$ nA               |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>Note 2, $T_J = 125^\circ\text{C}$   |                       |      | 50 $\mu\text{A}$<br>1.5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 105A$ , Note 1                                    |                       |      | 14.5 $m\Omega$             |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)  | Characteristic Values |      |                         |
|--------------|--|-----------------------|------|-------------------------|
|              |  | Min.                  | Typ. | Max.                    |
| $g_{fs}$     | $V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1   | 60                    | 100  | S                       |
| $C_{iss}$    | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$   |                       | 16.2 | nF                      |
| $C_{oss}$    |  |                       | 2550 | pF                      |
| $C_{rss}$    |  |                       | 42   | pF                      |
| $R_{Gi}$     | Gate Input Resistance  |                       | 1.0  | $\Omega$                |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 105\text{A}$<br>$R_G = 1\Omega$ (External) |                       | 46   | ns                      |
| $t_r$        |  |                       | 25   | ns                      |
| $t_{d(off)}$ |  |                       | 94   | ns                      |
| $t_f$        |  |                       | 13   | ns                      |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 105\text{A}$   |                       | 268  | nC                      |
| $Q_{gs}$     |  |                       | 80   | nC                      |
| $Q_{gd}$     |  |                       | 72   | nC                      |
| $R_{thJC}$   |  |                       |      | $0.083^\circ\text{C/W}$ |
| $R_{thCS}$   |  | 0.05                  |      | $^\circ\text{C/W}$      |

### SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

| SYM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 1.240  | 1.255 | 31.50       | 31.88 |
| B   | .307   | .323  | 7.80        | 8.20  |
| C   | .161   | .169  | 4.09        | 4.29  |
| D   | .161   | .169  | 4.09        | 4.29  |
| E   | .161   | .169  | 4.09        | 4.29  |
| F   | .587   | .595  | 14.91       | 15.11 |
| G   | 1.186  | 1.193 | 30.12       | 30.30 |
| H   | 1.496  | 1.505 | 38.00       | 38.23 |
| J   | .460   | .481  | 11.68       | 12.22 |
| K   | .351   | .378  | 8.92        | 9.60  |
| L   | .030   | .033  | 0.76        | 0.84  |
| M   | .496   | .506  | 12.60       | 12.85 |
| N   | .990   | 1.001 | 25.15       | 25.42 |
| O   | .078   | .084  | 1.98        | 2.13  |
| P   | .195   | .235  | 4.95        | 5.97  |
| Q   | 1.045  | 1.059 | 26.54       | 26.90 |
| R   | .155   | .174  | 3.94        | 4.42  |
| S   | .186   | .191  | 4.72        | 4.85  |
| T   | .968   | .987  | 24.59       | 25.07 |
| U   | -.002  | .004  | -0.05       | 0.1   |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                        | Characteristic Values |      |               |
|----------|--|-----------------------|------|---------------|
|          |  | Min.                  | Typ. | Max.          |
| $I_s$    | $V_{GS} = 0\text{V}$   |                       |      | 210 A         |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$  |                       |      | 840 A         |
| $V_{SD}$ | $I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1   |                       |      | 1.5 V         |
| $t_{rr}$ | $I_F = 105\text{A}, -di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}, V_{GS} = 0\text{V}$ |                       |      | 250 ns        |
| $Q_{RM}$ |  |                       | 4.1  | $\mu\text{C}$ |
| $I_{RM}$ |  |                       | 28   | A             |

### Notes:

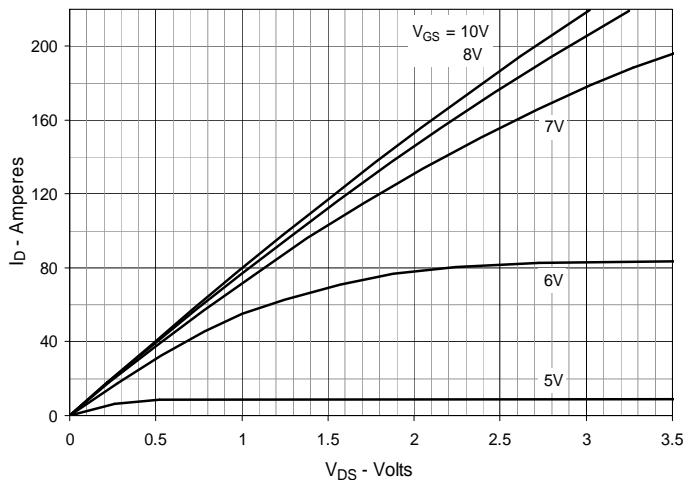
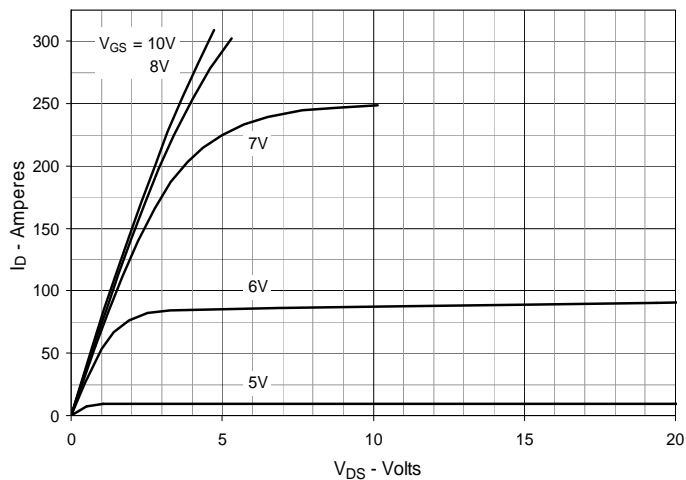
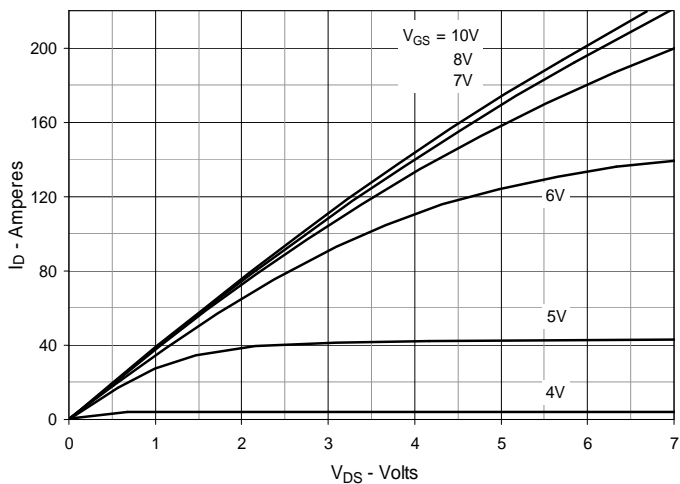
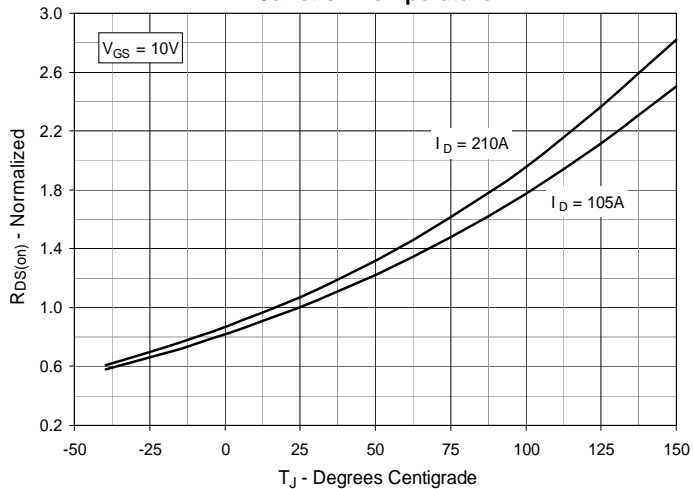
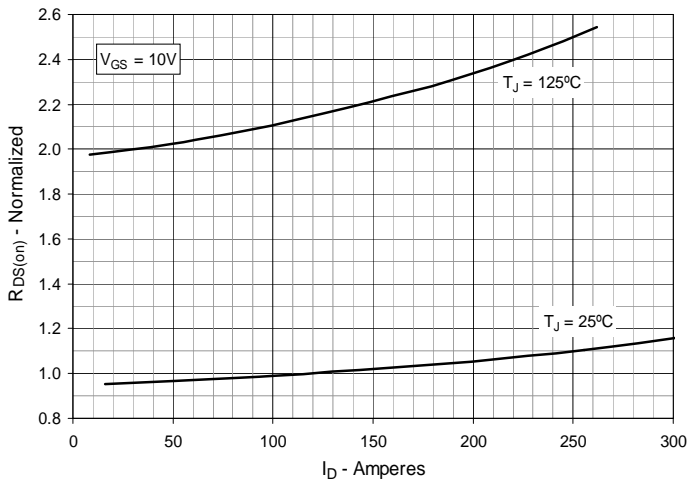
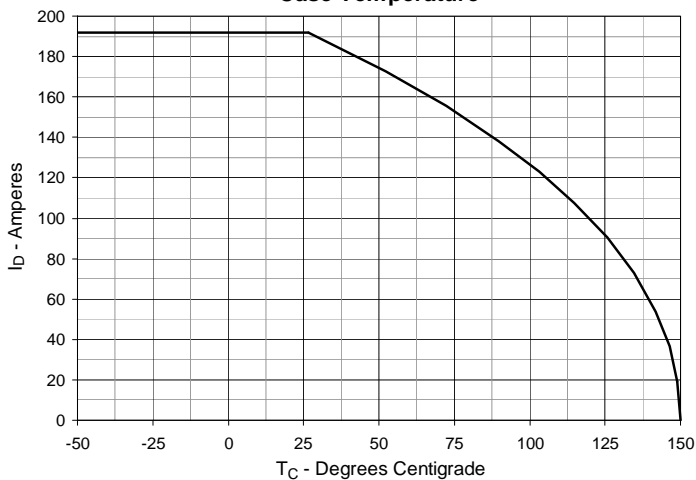
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Part must be heatsunk for high-temp  $I_{DSS}$  measurement.

### ADVANCE TECHNICAL INFORMATION

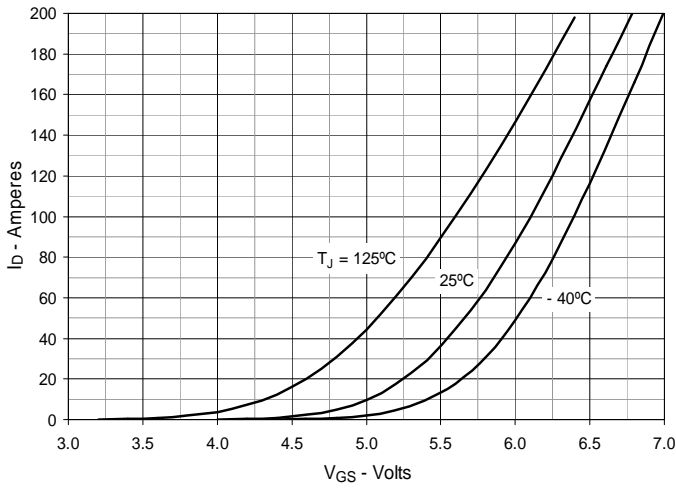
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

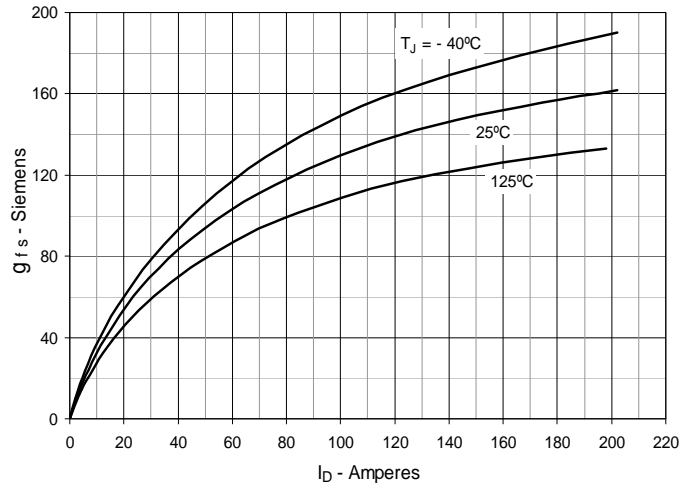
|  |           |           |           |           |              |              |              |              |              |             |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
|  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
|  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 105\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 105\text{A}$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


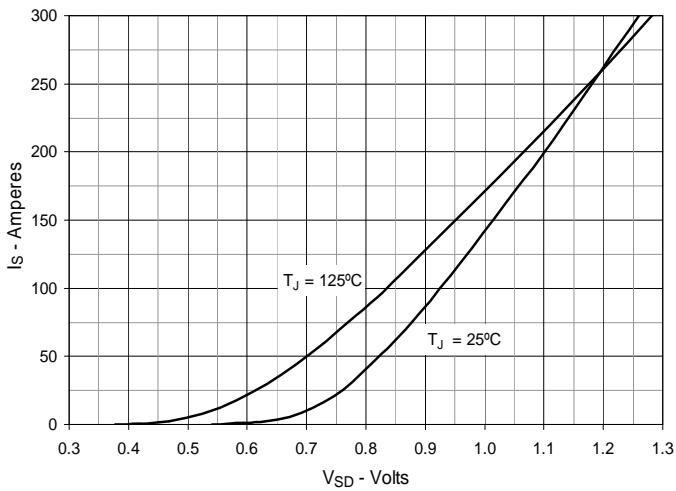
**Fig. 7. Input Admittance**



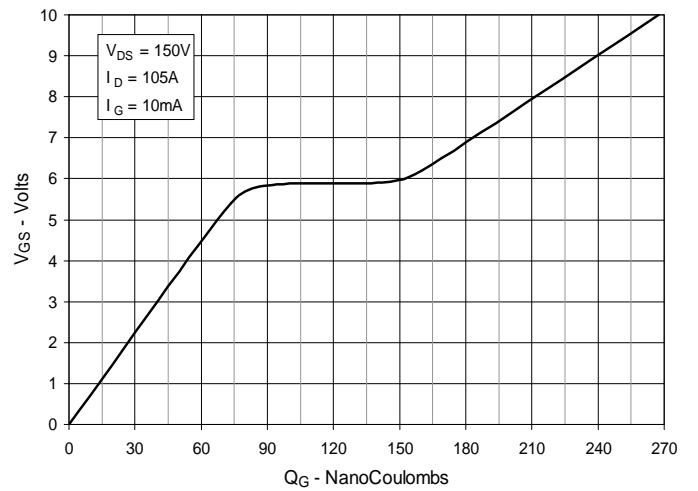
**Fig. 8. Transconductance**



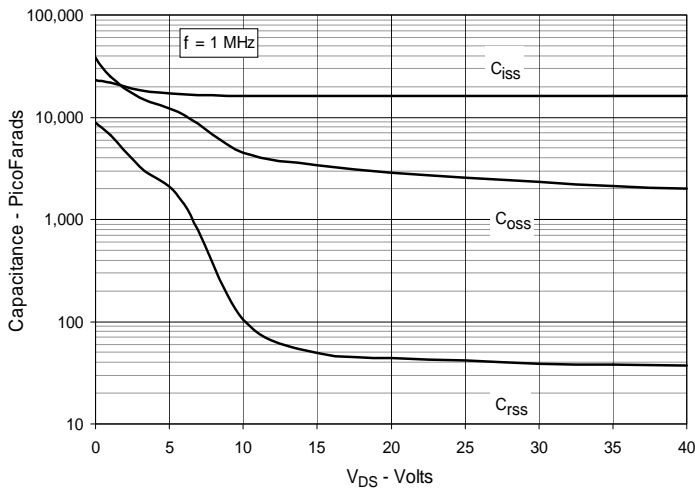
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

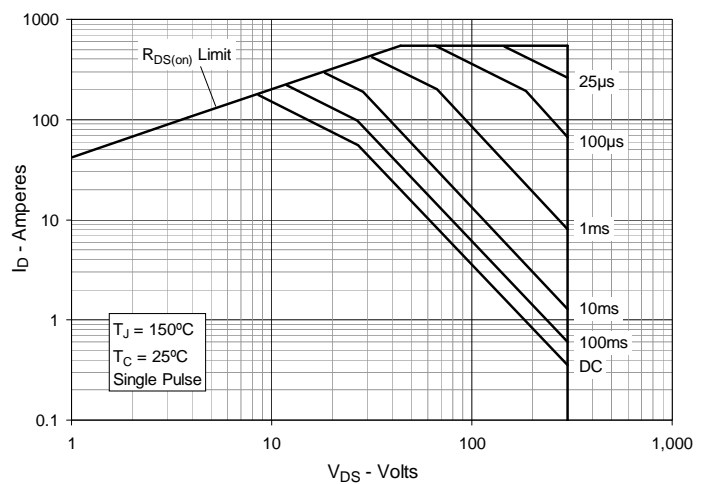


Fig. 13. Maximum Transient Thermal Impedance

